



PATENT
Docket No.: ACT-307DVA

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Art Unit: 2814

Examiner: Mai, Anh D.

Serial No.: 10/036,303

Filed: December 28, 2001

In Re Application of: Hawley, et al.

For: METHOD FOR FABRICATING AN MOS TRANSISTOR HAVING
IMPROVED TOTAL RADIATION-INDUCED LEAKAGE CURRENT

#12C Andot
x/e M. Brauns
6/4/03

Certificate of Mailing

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail, in an envelope addressed to MS Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450,

on 5/27/03

Signed

Martha N. Griffin

Martha N. Griffin

AMENDMENT AND RESPONSE TO OFFICE ACTION

MS Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In response to the Office Action mailed December 26, 2002, kindly amend
the above-identified application as follows.

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